

L1200-35xx

High Power InGaAsP NIR LED

L1200-35xx is an InGaAsP LED mounted on a metal stem and covered with epoxy resin or glass lens can.

On forward bias, it emits a spectral band of radiation which peaks at 1200nm.

Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	120	mW
Forward Current	IF	100	mA
Pulse Forward Current*	IFP	1000	mA
Reverse Voltage	VR	5	V
Operating Temperature	TOPR	-20 ~ +90	°C
Storage Temperature	TSTG	-30 ~+100	°C
Soldering Temperature**	TSOL	260	°C

* Duty=1% and Pulse Width=1μs

** Soldering condition must be completed within 3 second at 260°C.

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.10	1.40	V
Reverse Current	IR	VR=5V			10	uA
Peak Wavelength	λP	IF=50mA	1150	1200	1250	nm
Half Width	Δλ	IF=50mA		100		nm
Rise Time	tr	IF=50mA		10		ns
Fall Time	tf	IF=50mA		10		ns

Radiated Power[Ta=25°C]				
Type No.	Radiated Power* at IF=50mA (unit:mW)			Viewing Half Angle(θ1/2)
	Minimum	Typical	Maximum	
L1200-35K00		3.5		±50°
L1200-35K42		3.0		±6°
L1200-35M00		3.5		±50°
L1200-35M32		3.5		±15°
L1200-35T52		2.5		±55°

* Radiated Power is measured by Ando Optical Multi Meter AQ2140&AQ2742

Outer dimension (Unit: mm)

